

MOSFET - Power, Single N-Channel, SO-8FL 30 V, 78 A NTMFS4C024N

Features

- Low R_{DS(on)} to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- CPU Power Delivery
- DC-DC Converters

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

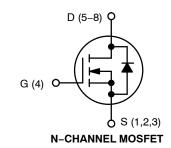
Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V_{GS}	±20	V
Continuous Drain		$T_A = 25^{\circ}C$	I _D	21.7	Α
Current R _{θJA} (Note 2)		$T_A = 80^{\circ}C$		16.3	
Power Dissipation $R_{\theta JA}$ (Note 2)		T _A = 25°C	P _D	2.57	W
Continuous Drain		$T_A = 25^{\circ}C$	I _D	34.8	Α
Current $R_{\theta JA} \le 10 \text{ s}$ (Note 2)		T _A = 80°C		26.0	
Power Dissipation $R_{\theta JA} \le 10 \text{ s (Note 2)}$	Steady	T _A = 25°C	P_{D}	6.6	V
Continuous Drain	State	$T_A = 25^{\circ}C$	I _D	11.9	Α
Current R _{θJA} (Note 3)		$T_A = 80^{\circ}C$		8.9	
Power Dissipation $R_{\theta JA}$ (Note 3)		T _A = 25°C	P _D	0.77	W
Continuous Drain		T _C = 25°C	Ι _D	78	Α
Current R _{θJC} (Note 2)		T _C =80°C		58	
Power Dissipation $R_{\theta JC}$ (Note 2)		T _C = 25°C	P _D	33	V
Pulsed Drain Current	$T_{A} = 25^{\circ}$	C, t _p = 10 μs	I _{DM}	174	Α
Current Limited by Pac	kage	T _A = 25°C	I _{Dmax}	80	Α
Operating Junction and Range	Operating Junction and Storage Temperature Range			-55 to +150	°C
Source Current (Body Diode)			I _S	30	Α
Drain to Source dV/dt			dV/d _t	7.0	V/ns
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^{\circ}C$, $V_{GS} = 20$ V, $I_L = 41$ A _{pk} , $L = 0.1$ mH, $R_{GS} = 25$ Ω) (Note 4)			E _{AS}	84	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 2. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
- 3. Surface-mounted on FR4 board using the minimum recommended pad size.
- 4. This is the absolute maximum ratings. Parts are 100% tested at $T_J=25^{\circ}C$, $V_{GS}=20$ V, $I_L=29$ A, $E_{AS}=42$ mJ.

1

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D MAX
30 V	2.8 mΩ @ 10 V	
30 V	4.0 mΩ @ 4.5 V	76 A



MARKING DIAGRAM



A = Assembly Location

Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping [†]
NTMFS4C024NT1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel

DISCONTINUED (Note 1)

NTMFS4C024NT3G	SO-8 FL	5000 /	
	(Pb-Free)	Tape & Reel	

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- DISCONTINUED: These devices are not recommended for new design. Please contact your onsemi representative for information. The most current information on these devices may be available on www.onsemi.com.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{ heta JC}$	3.8	
Junction-to-Ambient - Steady State (Note 5)	$R_{\theta JA}$	48.6	°C/W
Junction-to-Ambient - Steady State (Note 6)	$R_{\theta JA}$	161.7	*C/VV
Junction-to-Ambient - (t ≤ 10 s) (Note 5)	$R_{\theta JA}$	19	

ELECTRICAL CHARACTERISTICS (T_{.1} = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•		•	•	•	•
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30			V
Drain-to-Source Breakdown Voltage (transient)	V _{(BR)DSSt}	V _{GS} = 0 V, I _{D(aval)} = 12.6 A, T _{case} = 25°C, t _{transient} = 100 ns		34			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} / T _J				12		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$,	T _J = 25°C			1.0	μΑ
		V _{DS} = 24 V	T _J = 125°C			10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _G	_S = ±20 V			±100	nA
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_{D}$	= 250 μΑ	1.3		2.2	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J				5.1		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A		2.3	2.8	
		V _{GS} = 4.5 V	I _D = 30 A		3.3	4.0	mΩ
Forward Transconductance	9FS	V _{DS} = 1.5 V, I _D = 15 A			68		S
Gate Resistance	R_{G}	T _A = 25°C		0.3	1.0	2.0	Ω
CHARGES AND CAPACITANCES							
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 15 V			1972		pF
Output Capacitance	C _{OSS}				1215		
Reverse Transfer Capacitance	C _{RSS}				59		
Capacitance Ratio	C _{RSS} /C _{ISS}	V _{GS} = 0 V, V _{DS} = 1	5 V, f = 1 MHz		0.030		
Total Gate Charge	Q _{G(TOT)}				14		
Threshold Gate Charge	Q _{G(TH)}				3.3		C
Gate-to-Source Charge	Q_{GS}	V _{GS} = 4.5 V, V _{DS} =	15 V; I _D = 30 A		6.0		nC
Gate-to-Drain Charge	Q_{GD}	1			5.0		
Gate Plateau Voltage	V_{GP}	1			3.1		٧
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 15 V; I _D = 30 A			30		nC
SWITCHING CHARACTERISTICS (Note 8)							
Turn-On Delay Time	t _{d(ON)}				11		
Rise Time	t _r	V_{GS} = 4.5 V, V_{DS} = 15 V, I_{D} = 15 A, R_{G} = 3.0 Ω			32		
Turn-Off Delay Time	t _{d(OFF)}				21		ns
Fall Time	t _f				7.0		1

^{5.} Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.6. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
SWITCHING CHARACTERISTICS (N	ote 8)				•	•	
Turn-On Delay Time	t _{d(ON)}	V_{GS} = 10 V, V_{DS} = 15 V, I_{D} = 15 A, R_{G} = 3.0 Ω			8.0		- ns
Rise Time	t _r				26		
Turn-Off Delay Time	t _{d(OFF)}				26		
Fall Time	t _f				5.0		
DRAIN-SOURCE DIODE CHARACTE	ERISTICS						
Forward Diode Voltage	V_{SD}	V _{GS} = 0 V,	T _J = 25°C		0.77	1.1	.,
		$V_{GS} = 0 \text{ V},$ $I_{S} = 10 \text{ A}$ $I_{J} = 25^{\circ}\text{C}$ $I_{J} = 125^{\circ}\text{C}$		0.62			
Reverse Recovery Time	t _{RR}	$V_{GS} = 0 \text{ V, } dI_{S}/dt = 100 \text{ A/}\mu\text{s,}$ $I_{S} = 30 \text{ A}$			40.2		
Charge Time	t _a				20.3		ns
Discharge Time	t _b				19.9		
Reverse Recovery Charge	Q _{RR}				30.2		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Pulse Test: pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$.

8. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

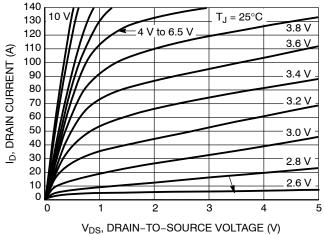


Figure 1. On–Region Characteristics

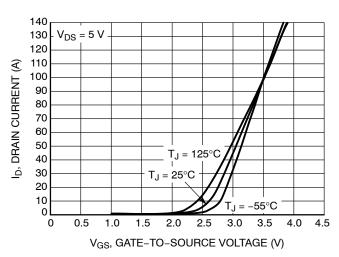


Figure 2. Transfer Characteristics

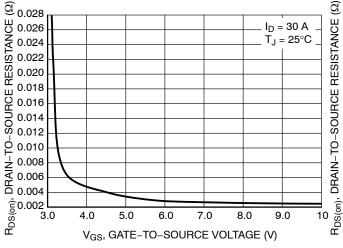


Figure 3. On–Resistance vs. V_{GS}

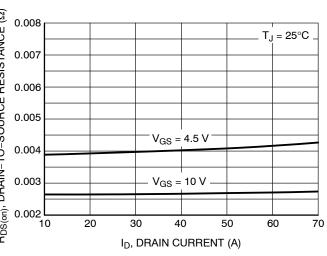


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

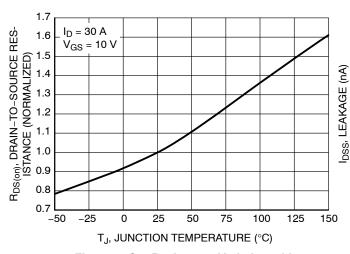


Figure 5. On–Resistance Variation with Temperature

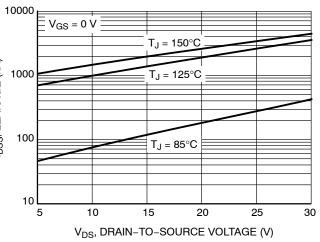


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

V_{GS}, GATE-TO-SOURCE VOLTAGE (V)

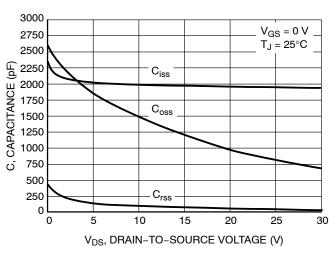


Figure 7. Capacitance Variation

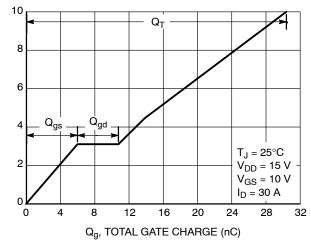


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

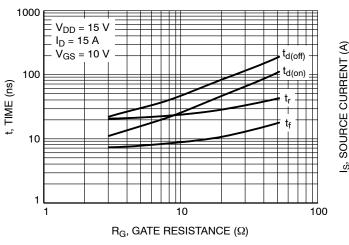


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

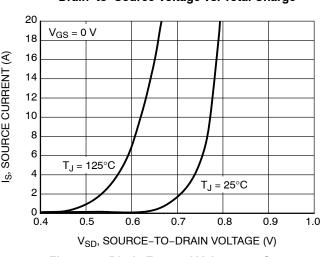


Figure 10. Diode Forward Voltage vs. Current

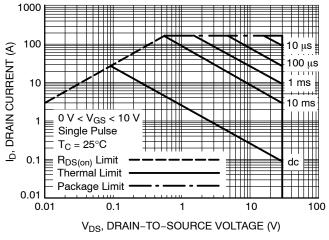


Figure 11. Maximum Rated Forward Biased Safe Operating Area

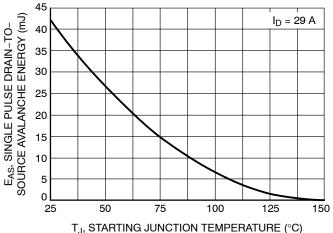


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

TYPICAL CHARACTERISTICS

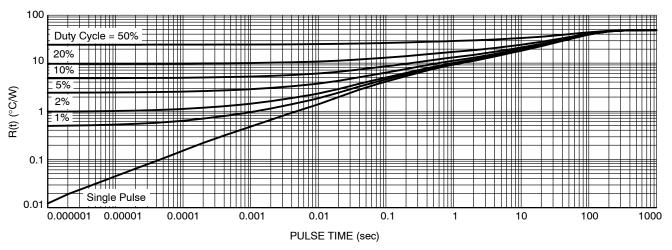


Figure 13. Thermal Response

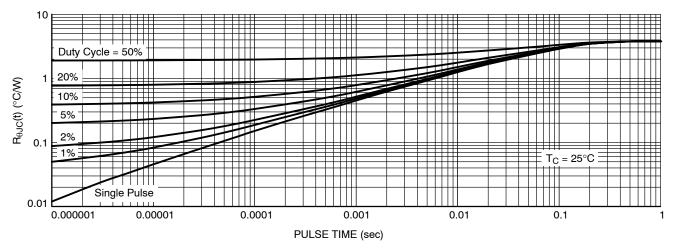


Figure 14. Thermal Response

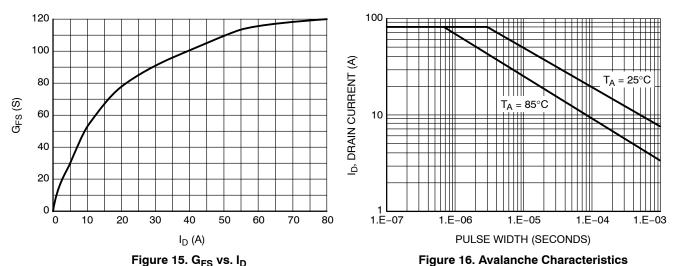


Figure 16. Avalanche Characteristics





DFN5 5x6, 1.27P (SO-8FL) CASE 488AA **ISSUE N**

DATE 25 JUN 2018

NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION D1 AND E1 DO NOT INCLUDE
- MOLD FLASH PROTRUSIONS OR GATE BURRS

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.90	1.00	1.10	
A1	0.00		0.05	
b	0.33	0.41	0.51	
С	0.23	0.28	0.33	
D	5.00	5.15	5.30	
D1	4.70	4.90	5.10	
D2	3.80	4.00	4.20	
E	6.00	6.15	6.30	
E1	5.70	5.90	6.10	
E2	3.45	3.65	3.85	
е		1.27 BSC	;	
G	0.51	0.575	0.71	
K	1.20	1.35	1.50	
L	0.51	0.575	0.71	
L1	0.125 REF			
М	3.00	3.40	3.80	
θ	0 °		12 °	

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code

= Assembly Location Α

= Lot Traceability

Υ = Year W = Work Week

ZZ

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.





DETAIL A

SIDE VIEW

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)		PAGE 1 OF 1	

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